

Sidong Lei

List of Publications by Year in descending order

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329
papers

26,279
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8749

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all docs

335
docs citations

335
times ranked

25167
citing authors

#	ARTICLE	IF	CITATIONS
1	Thickness-Driven Quantum Anomalous Hall Phase Transition in Magnetic Topological Insulator Thin Films. ACS Nano, 2022, 16, 1134-1141.	7.3	4
2	Manipulating Exchange Bias in a Van der Waals Ferromagnet. Advanced Materials, 2022, 34, e2105266.	11.1	16
3	Topological spintronics and magnetoelectronics. Nature Materials, 2022, 21, 15-23.	13.3	101
4	Current-induced Néel order switching facilitated by magnetic phase transition. Nature Communications, 2022, 13, 1629.	5.8	13
5	A Van der Waals Interface Hosting Two Groups of Magnetic Skyrmions. Advanced Materials, 2022, 34, e2110583.	11.1	37
6	Field-free approaches for deterministic spin-orbit torque switching of the perpendicular magnet. Materials Futures, 2022, 1, 022201.	3.1	20
7	van der Waals Semiconductor Empowered Vertical Color Sensor. ACS Nano, 2022, 16, 8619-8629.	7.3	5
8	Observation of Hole Transfer in MoS ₂ /WS ₂ Van der Waals Heterostructures. ACS Photonics, 2022, 9, 1709-1716.	3.2	10
9	Efficient Spin-Orbit Torque Switching of Perpendicular Magnetization using Topological Insulators with High Thermal Tolerance. Advanced Electronic Materials, 2022, 8, .	2.6	6
10	Comprehensive Study of the Current-Induced Spin-Orbit Torque Perpendicular Effective Field in Asymmetric Multilayers. Nanomaterials, 2022, 12, 1887.	1.9	4
11	Micro-magnetoelastic modeling of Terfenol-D for spintronics. Journal of Applied Physics, 2022, 131, 234101.	1.1	1
12	Discovery of Graphene-Water Membrane Structure: Toward High-Quality Graphene Process. Advanced Science, 2022, 9, .	5.6	6
13	Adaptive MRAM Write and Read with MTJ Variation Monitor. IEEE Transactions on Emerging Topics in Computing, 2021, 9, 402-413.	3.2	8
14	Faraday Rotation Due to Quantum Anomalous Hall Effect in Cr-Doped (Bi,Sb) ₂ Te ₃ . Crystals, 2021, 11, 154.	1.0	2
15	Néel-Type Elliptical Skyrmions in a Laterally Asymmetric Magnetic Multilayer. Advanced Materials, 2021, 33, e2006924.	11.1	32
16	Experimental demonstration of voltage-gated spin-orbit torque switching in an antiferromagnet/ferromagnet structure. Physical Review B, 2021, 103, .	1.1	14
17	Temperature dependence of spin-orbit torque-driven magnetization switching in <i>in situ</i> grown Bi ₂ Te ₃ /MnTe heterostructures. Applied Physics Letters, 2021, 118, .	1.5	12
18	Large spin to charge conversion in antiferromagnetic Weyl semimetal Mn ₃ Sn. APL Materials, 2021, 9, .	2.2	11

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19	Broadband photocurrent spectroscopy and temperature dependence of band gap of few-layer indium selenide (InSe). <i>Emergent Materials</i> , 2021, 4, 1029-1036.	3.2	7
20	Bulk dissipation in the quantum anomalous Hall effect. <i>APL Materials</i> , 2021, 9, 081116.	2.2	12
21	Single-molecule photocatalytic dynamics at individual defects in two-dimensional layered materials. <i>Science Advances</i> , 2021, 7, eabj4452.	4.7	22
22	Chiral Symmetry Breaking for Deterministic Switching of Perpendicular Magnetization by Spin-Orbit Torque. <i>Nano Letters</i> , 2021, 21, 515-521.	4.5	64
23	Reconfigurable Multivalued Logic Functions of a Silicon Ellipsoidal Quantum-Dot Transistor Operating at Room Temperature. <i>ACS Nano</i> , 2021, 15, 18483-18493.	7.3	8
24	A Calibration-Free In-Memory True Random Number Generator Using Voltage-Controlled MRAM. , 2021, , .		0
25	Magnetic memory driven by topological insulators. <i>Nature Communications</i> , 2021, 12, 6251.	5.8	67
26	Room-Temperature Ferromagnetism of Single-Layer MoS ₂ Induced by Antiferromagnetic Proximity of Yttrium Iron Garnet. <i>Advanced Quantum Technologies</i> , 2021, 4, 2000104.	1.8	9
27	A Calibration-Free In-Memory True Random Number Generator Using Voltage-Controlled MRAM. , 2021, , .		1
28	Conversion between spin and charge currents in topological-insulator/nonmagnetic-metal systems. <i>Physical Review B</i> , 2021, 104, .	1.1	3
29	Spectroscopic fingerprint of chiral Majorana modes at the edge of a quantum anomalous Hall insulator/superconductor heterostructure. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2020, 117, 238-242.	3.3	22
30	Observation of Quantum Anomalous Hall Effect and Exchange Interaction in Topological Insulator/Antiferromagnet Heterostructure. <i>Advanced Materials</i> , 2020, 32, e2001460.	11.1	27
31	Above Room-Temperature Ferromagnetism in Wafer-Scale Two-Dimensional van der Waals Fe ₃ GeTe ₂ Tailored by a Topological Insulator. <i>ACS Nano</i> , 2020, 14, 10045-10053.	7.3	124
32	Ferrimagnetic Skyrmions in Topological Insulator/Ferrimagnet Heterostructures. <i>Advanced Materials</i> , 2020, 32, e2003380.	11.1	41
33	Modulation of thermal stability and spin-orbit torque in IrMn/CoFeB/MgO structures through atom thick W insertion. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	13
34	Large exchange splitting in monolayer graphene magnetized by an antiferromagnet. <i>Nature Electronics</i> , 2020, 3, 604-611.	13.1	36
35	Termination switching of antiferromagnetic proximity effect in topological insulator. <i>Science Advances</i> , 2020, 6, eaaz8463.	4.7	20
36	Enhancement of the spin-orbit torque efficiency in W/Cu/CoFeB heterostructures via interface engineering. <i>Applied Physics Letters</i> , 2020, 117, 082409.	1.5	6

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37	Exchange bias switching in an antiferromagnet/ferromagnet bilayer driven by spin-orbit torque. <i>Nature Electronics</i> , 2020, 3, 757-764.	13.1	99
38	Spin-orbit torques in structures with asymmetric damping layers. <i>Applied Physics Letters</i> , 2020, 117, 182403.	1.5	13
39	Interfacial spin transmission and spin-orbit torques in as-grown and annealed W/Co ₂ FeAl/MgO multilayers. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	8
40	Topological quantum materials. <i>MRS Bulletin</i> , 2020, 45, 373-379.	1.7	3
41	Probing the low-temperature limit of the quantum anomalous Hall effect. <i>Science Advances</i> , 2020, 6, eaaz3595.	4.7	35
42	Study of the perpendicular magnetic anisotropy, spin-orbit torque, and Dzyaloshinskii-Moriya interaction in the heavy metal/CoFeB bilayers with Ir ₂₂ Mn ₇₈ insertion. <i>Applied Physics Letters</i> , 2020, 116, 242407.	1.5	8
43	Criticality or Supersymmetry Breaking?. <i>Symmetry</i> , 2020, 12, 805.	1.1	7
44	Deterministic Spin-Orbit Torque Switching by a Light-Metal Insertion. <i>Nano Letters</i> , 2020, 20, 3703-3709.	4.5	52
45	Creation and annihilation of non-volatile fixed magnetic skyrmions using voltage control of magnetic anisotropy. <i>Nature Electronics</i> , 2020, 3, 539-545.	13.1	76
46	Topology-Dependent Brownian Gyromotion of a Single Skyrmion. <i>Physical Review Letters</i> , 2020, 125, 027206.	2.9	50
47	Strongly Surface State Carrier-Dependent Spin-Orbit Torque in Magnetic Topological Insulators. <i>Advanced Materials</i> , 2020, 32, e1907661.	11.1	29
48	Resistive switching materials for information processing. <i>Nature Reviews Materials</i> , 2020, 5, 173-195.	23.3	668
49	Influence of channel thickness on charge transport behavior of multi-layer indium selenide (InSe) field-effect transistors. <i>2D Materials</i> , 2020, 7, 025030.	2.0	7
50	Anomalous Conductivity Switch Observed in Treated Hafnium Diselenide Transistors. <i>Advanced Electronic Materials</i> , 2020, 6, 1901246.	2.6	9
51	Spin transmission in IrMn through measurements of spin Hall magnetoresistance and spin-orbit torque. <i>Physical Review B</i> , 2020, 101, .	1.1	11
52	Record thermopower found in an IrMn-based spintronic stack. <i>Nature Communications</i> , 2020, 11, 2023.	5.8	16
53	How surface tension matters in polymer-free graphene transfer. <i>Oxford Open Materials Science</i> , 2020, 1, .	0.5	0
54	Role of layer thickness and field-effect mobility on photoresponsivity of indium selenide (InSe)-based phototransistors. <i>Oxford Open Materials Science</i> , 2020, 1, .	0.5	3

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55	Two-dimensional spintronics for low-power electronics. <i>Nature Electronics</i> , 2019, 2, 274-283.	13.1	334
56	Spin-Orbit Torque Switching of a Nearly Compensated Ferrimagnet by Topological Surface States. <i>Advanced Materials</i> , 2019, 31, e1901681.	11.1	81
57	Field-Free Spin-Orbit Torque Switching of Perpendicular Magnetization by the Rashba Interface. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 39369-39375.	4.0	45
58	Gate-Induced Metal-Insulator Transition in 2D van der Waals Layers of Copper Indium Selenide Based Field-Effect Transistors. <i>ACS Nano</i> , 2019, 13, 13413-13420.	7.3	20
59	Predictive Materials Design of Magnetic Random-Access Memory Based on Nanoscale Atomic Structure and Element Distribution. <i>Nano Letters</i> , 2019, 19, 8621-8629.	4.5	22
60	Voltage-Controlled Magnetic Anisotropy in Heterostructures with Atomically Thin Heavy Metals. <i>Physical Review Applied</i> , 2019, 12, .	1.5	22
61	Experimental Demonstration of Spintronic Broadband Microwave Detectors and Their Capability for Powering Nanodevices. <i>Physical Review Applied</i> , 2019, 11, .	1.5	49
62	Failure Mechanism Analysis of SiC MOSFETs in Unclamped Inductive Switching Conditions. , 2019, , .		24
63	Giant Charge-to-Spin Conversion Efficiency in SrTiO_3 -Based Electron Gas Interface. <i>Physical Review Applied</i> , 2019, 12, .	1.5	28
64	Interfacial States and Fano-Feshbach Resonance in Graphene-Silicon Vertical Junction. <i>Nano Letters</i> , 2019, 19, 6765-6771.	4.5	2
65	Unidirectional Magneto-Resistance in Modulation-Doped Magnetic Topological Insulators. <i>Nano Letters</i> , 2019, 19, 692-698.	4.5	20
66	Electric Double Layer Field-Effect Transistors Using Two-Dimensional (2D) Layers of Copper Indium Selenide ($\text{CuIn}_7\text{Se}_{11}$). <i>Electronics (Switzerland)</i> , 2019, 8, 645.	1.8	10
67	Compact Model for Negative Capacitance Enhanced Spintronics Devices. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2795-2801.	1.6	4
68	Topological Hall effect at above room temperature in heterostructures composed of a magnetic insulator and a heavy metal. <i>Nature Electronics</i> , 2019, 2, 182-186.	13.1	117
69	Spin-orbit torque from a ferromagnetic metal. <i>Physical Review B</i> , 2019, 99, .	1.1	49
70	Control of Spin-Wave Damping in YIG Using Spin Currents from Topological Insulators. <i>Physical Review Applied</i> , 2019, 11, .	1.5	30
71	Exploring interfacial exchange coupling and sublattice effect in heavy metal/ferrimagnetic insulator heterostructures using Hall measurements, x-ray magnetic circular dichroism, and neutron reflectometry. <i>Physical Review B</i> , 2019, 99, .	1.1	39
72	Large Tunneling Magnetoresistance in $\text{VSe}_2/\text{MoS}_2$ Magnetic Tunnel Junction. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 17647-17653.	4.0	65

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73	Colossal electric field control of magnetic anisotropy at ferromagnetic interfaces induced by iridium overlayer. <i>Physical Review B</i> , 2019, 99, .	1.1	24
74	Room-Temperature Spin-Orbit Torque from Topological Surface States. <i>Physical Review Letters</i> , 2019, 123, 207205.	2.9	129
75	Generation and Hall effect of skyrmions enabled using nonmagnetic point contacts. <i>Physical Review B</i> , 2019, 100, .	1.1	14
76	Heat-assisted microwave amplifier. <i>Nature Nanotechnology</i> , 2019, 14, 9-11.	15.6	2
77	Single-spin sensing of domain-wall structure and dynamics in a thin-film skyrmion host. <i>Physical Review Materials</i> , 2019, 3, .	0.9	27
78	Analysis and Compact Modeling of Magnetic Tunnel Junctions Utilizing Voltage-Controlled Magnetic Anisotropy. <i>IEEE Transactions on Magnetics</i> , 2018, 54, 1-9.	1.2	27
79	Voltage-Controlled Magnetic Tunnel Junctions for Processing-In-Memory Implementation. <i>IEEE Electron Device Letters</i> , 2018, 39, 440-443.	2.2	29
80	Interfacial Dzyaloshinskii-Moriya Interaction: Effect of $\frac{5}{d}$ Band Filling and Correlation with Spin Mixing Conductance. <i>Physical Review Letters</i> , 2018, 120, 157204.	2.9	116
81	$\frac{2}{Te}$ Physical Review B, 2018, 97, .	1.1	12
82	Room-Temperature Skyrmions in an Antiferromagnet-Based Heterostructure. <i>Nano Letters</i> , 2018, 18, 980-986.	4.5	98
83	A Study of Vertical Transport through Graphene toward Control of Quantum Tunneling. <i>Nano Letters</i> , 2018, 18, 682-688.	4.5	13
84	Interface control of domain wall depinning field. <i>AIP Advances</i> , 2018, 8, .	0.6	4
85	Fast photoresponse and high detectivity in copper indium selenide (CuIn ₇ Se ₁₁) phototransistors. <i>2D Materials</i> , 2018, 5, 015001.	2.0	24
86	Spintronic devices for low energy dissipation. , 2018, , .		5
87	Near-Field Coupled Integrable Two-Dimensional InSe Photosensor on Optical Fiber. <i>ACS Nano</i> , 2018, 12, 12571-12577.	7.3	19
88	Voltage-controlled magnetoelectric memory and logic devices. <i>MRS Bulletin</i> , 2018, 43, 970-977.	1.7	47
89	Strain-Mediated Spin-Orbit-Torque Switching for Magnetic Memory. <i>Physical Review Applied</i> , 2018, 10, .	1.5	31
90	Spin-Torque Ferromagnetic Resonance in $W_{1-x}Co_xFe$		23

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91	Correlation between the Dzyaloshinskii-Moriya interaction and spin-mixing conductance at an antiferromagnet/ferromagnet interface. <i>Physical Review B</i> , 2018, 98, .	1.1	13
92	Part-per-million quantization and current-induced breakdown of the quantum anomalous Hall effect. <i>Physical Review B</i> , 2018, 98, .	1.1	65
93	Role of dimensional crossover on spin-orbit torque efficiency in magnetic insulator thin films. <i>Nature Communications</i> , 2018, 9, 3612.	5.8	84
94	Topological Transitions Induced by Antiferromagnetism in a Thin-Film Topological Insulator. <i>Physical Review Letters</i> , 2018, 121, 096802.	2.9	42
95	Investigation on single pulse avalanche failure of 900V SiC MOSFETs. , 2018, , .		14
96	Layer-by-layer hybrid chemical doping for high transmittance uniformity in graphene-polymer flexible transparent conductive nanocomposite. <i>Scientific Reports</i> , 2018, 8, 10259.	1.6	18
97	Enhancement of Perpendicular Magnetic Anisotropy Through Fe Insertion at the CoFe/W Interface. <i>IEEE Transactions on Magnetics</i> , 2018, 54, 1-5.	1.2	6
98	Exchange-biasing topological charges by antiferromagnetism. <i>Nature Communications</i> , 2018, 9, 2767.	5.8	61
99	Proximity-Induced Magnetic Order in a Transferred Topological Insulator Thin Film on a Magnetic Insulator. <i>ACS Nano</i> , 2018, 12, 5042-5050.	7.3	41
100	Large Room Temperature Charge-to-Spin Conversion Efficiency in Topological Insulator/CoFeB bilayers. , 2018, , .		4
101	High photoresponse of individual WS ₂ nanowire-nanoflake hybrid materials. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	7
102	A Basic Phase Diagram of Neuronal Dynamics. <i>Neural Computation</i> , 2018, 30, 2418-2438.	1.3	2
103	Nanoengineering of an Si/MnGe quantum dot superlattice for high Curie-temperature ferromagnetism. <i>Nanoscale</i> , 2017, 9, 3086-3094.	2.8	13
104	Giant interfacial perpendicular magnetic anisotropy in MgO/CoFe/capping layer structures. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	73
105	A Word Line Pulse Circuit Technique for Reliable Magnetoelectric Random Access Memory. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2017, 25, 2027-2034.	2.1	15
106	Joule Heating Effect on Field-Free Magnetization Switching by Spin-Orbit Torque in Exchange-Biased Systems. <i>Physical Review Applied</i> , 2017, 7, .	1.5	48
107	Enhancement of voltage-controlled magnetic anisotropy through precise control of Mg insertion thickness at CoFeB MgO interface. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	92
108	Direct growth of MoS ₂ single crystals on polyimide substrates. <i>2D Materials</i> , 2017, 4, 021028.	2.0	39

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109	Interfacial Perpendicular Magnetic Anisotropy in Sub-20 nm Tunnel Junctions for Large-Capacity Spin-Transfer Torque Magnetic Random-Access Memory. <i>IEEE Magnetics Letters</i> , 2017, 8, 1-5.	0.6	25
110	Hybrid VC-MTJ/CMOS non-volatile stochastic logic for efficient computing. , 2017, , .		10
111	Observation of Quantum Hall effect in an ultra-thin (Bi _{0.53} Sb _{0.47}) ₂ Te ₃ film. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	12
112	Synthesis of large-scale atomic-layer SnS ₂ through chemical vapor deposition. <i>Nano Research</i> , 2017, 10, 2386-2394.	5.8	124
113	Efficient Excitation of High-Frequency Exchange-Dominated Spin Waves in Periodic Ferromagnetic Structures. <i>Physical Review Applied</i> , 2017, 7, .	1.5	22
114	Room-Temperature Skyrmion Shift Device for Memory Application. <i>Nano Letters</i> , 2017, 17, 261-268.	4.5	227
115	Atomic-Monolayer Two-Dimensional Lateral Quasi-Heterojunction Bipolar Transistors with Resonant Tunneling Phenomenon. <i>ACS Nano</i> , 2017, 11, 11015-11023.	7.3	45
116	Effects of Cd vacancies and unconventional spin dynamics in the Dirac semimetal Cd ₃ As ₂ . <i>Journal of Chemical Physics</i> , 2017, 147, 084706.	1.2	6
117	Stateful Reconfigurable Logic via a Single-Voltage-Gated Spin Hall-Effect Driven Magnetic Tunnel Junction in a Spintronic Memory. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4295-4301.	1.6	76
118	Partial spin absorption induced magnetization switching and its voltage-assisted improvement in an asymmetrical all spin logic device at the mesoscopic scale. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	14
119	Voltage induced artificial ferromagnetic-antiferromagnetic ordering in synthetic multiferroics. <i>Journal of Applied Physics</i> , 2017, 122, 224102.	1.1	7
120	Anomalous Nernst effect in Ir ₂₂ Mn ₇₈ /Co ₂₀ Fe ₆₀ B ₂₀ /MgO layers with perpendicular magnetic anisotropy. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	24
121	Zero-field edge plasmons in a magnetic topological insulator. <i>Nature Communications</i> , 2017, 8, 1836.	5.8	32
122	Large voltage-controlled magnetic anisotropy in the SrTiO ₃ /Fe/Cu structure. <i>Applied Physics Letters</i> , 2017, 111, 152403.	1.5	16
123	Tayi et al. reply. <i>Nature</i> , 2017, 547, E14-E15.	13.7	3
124	Dzyaloshinskii-Moriya Interaction across an Antiferromagnet-Ferromagnet Interface. <i>Physical Review Letters</i> , 2017, 119, 027202.	2.9	75
125	Deficiency of the bulk spin Hall effect model for spin-orbit torques in magnetic-insulator/heavy-metal heterostructures. <i>Physical Review B</i> , 2017, 95, .	1.1	23
126	Tailoring exchange couplings in magnetic topological-insulator/antiferromagnet heterostructures. <i>Nature Materials</i> , 2017, 16, 94-100.	13.3	137

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127	Characterization of tin(II) sulfide defects/vacancies and correlation with their photocurrent. Nano Research, 2017, 10, 218-228.	5.8	8
128	Imaging the motion of electrons across semiconductor heterojunctions. Nature Nanotechnology, 2017, 12, 36-40.	15.6	124
129	Direct observation of the skyrmion Hall effect. Nature Physics, 2017, 13, 162-169.	6.5	858
130	Chiral transport along magnetic domain walls in the quantum anomalous Hall effect. Npj Quantum Materials, 2017, 2, .	1.8	37
131	Novel Magnetic Tunneling Junction Memory Cell With Negative Capacitance-Amplified Voltage-Controlled Magnetic Anisotropy Effect. IEEE Transactions on Electron Devices, 2017, 64, 4919-4927.	1.6	6
132	Leveraging nMOS Negative Differential Resistance for Low Power, High Reliability Magnetic Memory. IEEE Transactions on Electron Devices, 2017, 64, 4084-4090.	1.6	6
133	Topological supersymmetry breaking: The definition and stochastic generalization of chaos and the limit of applicability of statistics. Modern Physics Letters B, 2016, 30, 1650086.	1.0	11
134	Synthesis of Millimeter-Scale Transition Metal Dichalcogenides Single Crystals. Advanced Functional Materials, 2016, 26, 2009-2015.	7.8	152
135	Evidence for ferromagnetic coupling at the doped topological insulator/ferrimagnetic insulator interface. AIP Advances, 2016, 6, 055813.	0.6	8
136	Giant spin-torque diode sensitivity in the absence of bias magnetic field. Nature Communications, 2016, 7, 11259.	5.8	123
137	Competing effect of spin-orbit torque terms on perpendicular magnetization switching in structures with multiple inversion asymmetries. Scientific Reports, 2016, 6, 23956.	1.6	21
138	Mobile Néel skyrmions at room temperature: status and future. AIP Advances, 2016, 6, .	0.6	38
139	Spin-torque ferromagnetic resonance measurements utilizing spin Hall magnetoresistance in W/Co ₄₀ Fe ₄₀ B ₂₀ /MgO structures. Applied Physics Letters, 2016, 109, .	1.5	36
140	Influence of inserted Mo layer on the thermal stability of perpendicularly magnetized Ta/Mo/Co ₂₀ Fe ₆₀ B ₂₀ /MgO/Ta films. AIP Advances, 2016, 6, .	0.6	8
141	Enabling Ultrasensitive Photo-detection Through Control of Interface Properties in Molybdenum Disulfide Atomic Layers. Scientific Reports, 2016, 6, 39465.	1.6	4
142	Effect of heavy metal layer thickness on spin-orbit torque and current-induced switching in Hf CoFeB MgO structures. Applied Physics Letters, 2016, 109, .	1.5	33
143	Spin-orbit torques in perpendicularly magnetized Ir ₂₂ Mn ₇₈ /Co ₂₀ Fe ₆₀ B ₂₀ /MgO multilayer. Applied Physics Letters, 2016, 109, .	1.5	58
144	Wafer-scale monodomain films of spontaneously aligned single-walled carbon nanotubes. Nature Nanotechnology, 2016, 11, 633-638.	15.6	292

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145	Versatile Fabrication of Self-Aligned Nanoscale Hall Devices Using Nanowire Masks. Nano Letters, 2016, 16, 3109-3115.	4.5	4
146	Comparative Evaluation of Spin-Transfer-Torque and Magnetoelectric Random Access Memory. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2016, 6, 134-145.	2.7	81
147	Strain-Induced Electronic Structure Changes in Stacked van der Waals Heterostructures. Nano Letters, 2016, 16, 3314-3320.	4.5	122
148	Low-Cost, Large-Area, Facile, and Rapid Fabrication of Aligned ZnO Nanowire Device Arrays. ACS Applied Materials & Interfaces, 2016, 8, 13466-13471.	4.0	41
149	Atomic-Monolayer MoS ₂ Band-to-Band Tunneling Field-Effect Transistor. Small, 2016, 12, 5676-5683.	5.2	41
150	Strong Electrical Manipulation of Spin-Orbit Torque in Ferromagnetic Heterostructures. Advanced Electronic Materials, 2016, 2, 1600219.	2.6	37
151	Ultra-low-power, high-density spintronic programmable logic (SPL). , 2016, , .		2
152	Solid-Vapor Reaction Growth of Transition-Metal Dichalcogenide Monolayers. Angewandte Chemie - International Edition, 2016, 55, 10656-10661.	7.2	27
153	Solid-Vapor Reaction Growth of Transition-Metal Dichalcogenide Monolayers. Angewandte Chemie, 2016, 128, 10814-10819.	1.6	17
154	Spiral Growth of SnSe ₂ Crystals by Chemical Vapor Deposition. Advanced Materials Interfaces, 2016, 3, 1600383.	1.9	55
155	Interfacial control of Dzyaloshinskii-Moriya interaction in heavy metal/ferromagnetic metal thin film heterostructures. Physical Review B, 2016, 94, .	1.1	72
156	Self-aligned graphene oxide nanoribbon stack with gradient bandgap for visible-light photodetection. Nano Energy, 2016, 27, 114-120.	8.2	14
157	High performance silicon carbide avalanche-ultraviolet photodiode with dual operation models. Electronics Letters, 2016, 52, 1474-1476.	0.5	11
158	Strong Rashba-Edelstein Effect-Induced Spin-Orbit Torques in Monolayer Transition Metal Dichalcogenide/Ferromagnet Bilayers. Nano Letters, 2016, 16, 7514-7520.	4.5	247
159	Observing the interplay between surface and bulk optical nonlinearities in thin van der Waals crystals. Scientific Reports, 2016, 6, 22620.	1.6	42
160	Dual-mode operation of 2D material-base hot electron transistors. Scientific Reports, 2016, 6, 32503.	1.6	12
161	Enhancing electric-field control of ferromagnetism through nanoscale engineering of high-T _c Mn _x Ge _{1-x} nanomesh. Nature Communications, 2016, 7, 12866.	5.8	35
162	Spintronics Based on Topological Insulators. Spin, 2016, 06, 1640001.	0.6	77

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163	Direct Mapping of Charge Distribution during Lithiation of Ge Nanowires Using Off-Axis Electron Holography. Nano Letters, 2016, 16, 3748-3753.	4.5	34
164	Layer Engineering of 2D Semiconductor Junctions. Advanced Materials, 2016, 28, 5126-5132.	11.1	63
165	Low-Power, High-Density Spintronic Programmable Logic With Voltage-Gated Spin Hall Effect in Magnetic Tunnel Junctions. IEEE Magnetics Letters, 2016, 7, 1-5.	0.6	16
166	Room-Temperature Creation and Spin-Orbit Torque Manipulation of Skyrmions in Thin Films with Engineered Asymmetry. Nano Letters, 2016, 16, 1981-1988.	4.5	275
167	Surface functionalization of two-dimensional metal chalcogenides by Lewis acid-base chemistry. Nature Nanotechnology, 2016, 11, 465-471.	15.6	197
168	Co-doped Sb ₂ Te ₃ paramagnetic nanoplates. Journal of Materials Chemistry C, 2016, 4, 521-525.	2.7	13
169	Solid-Liquid Self-Adaptive Polymeric Composite. ACS Applied Materials & Interfaces, 2016, 8, 2142-2147.	4.0	6
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171	Resonant magneto-optic Kerr effect in the magnetic topological insulator Cr_2Te_3 . Physical Review B, 2015, 92, .	11.1	7
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